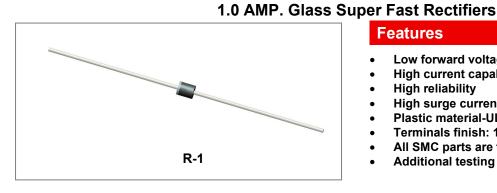


1E1G-1E8G

RoHS

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1E1G THRU 1E8G



Circuit Diagram



Features

- Low forward voltage drop
- High current capability
- **High reliability**
- High surge current capability
- Plastic material-UL 94V- flammability 0
- Terminals finish: 100% Pure Tin
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data

- Case: Molded plastic R-1
- Terminals: Plated leads solderable per MIL-STD-202, Method 208 guaranteed
- Polarity: Color band dentes cathode end
- Mounting Position: Any
- Lead Free: For RoHS/Lead Free Version

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristic	Symbol	1E1G	1E2G	1E3G	1E4G	1E5G	1E6G	1E8G	Units
Maximum repetitive peak reverse voltage Maximum DC blocking voltage	V _{RRM} V _{DC}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	420	V
Average Rectified Output Current (Note 1) $@T_L=75^{\circ}C$	I _(AV)	1.0			А				
I₂t Rating for Fusing (t < 8.3ms)	l²t		2.594				A²s		
Peak forward surge current 8.3ms single half sine- wave superimposed on rated load (JEDEC Method)	IFSM	25.0				А			
Maximum instantaneous forward voltage at 1.0A	VF	0.95		1.2	25	1.7	V		
Maximum DC reverse current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 125^{\circ}C$	I _{RM}	5.0 100			μA				
Maximum reverse recovery time (Note 2)	trr	35			ns				
Typical Junction Capacitance (Note 3)	CJ	30 25			pF				
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	40			°C/W				
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150			°C				

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A

3. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

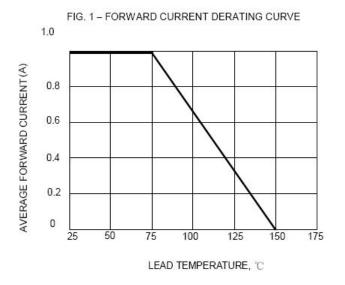
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Ratings and Characteristics Curves



INSTANTANEOUS FORWARD CURRENT, (A) 1E1G-1E4G 10 1E5G-1E6G 1E8G 1.0 TA = 25°C PULSE WIDTH 300us 0.1 2.0 0.4 1.4 1.6 1.8 0.2 0.6 0.8 1.0 1.2

FIG.2-TYPICAL FORWARD CHARACTERISTICS

100

INSTANTANEOUS FORWARD VOLTAGE (V)

FIG.4 - TYPICAL JUNCTION CAPACITANCE

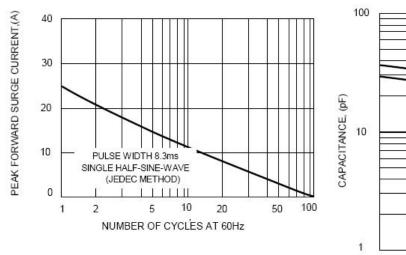
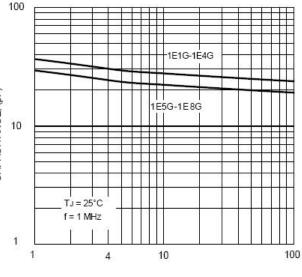


FIG. 3 - MAXIMUM NON-REPETITIVE SURGE CURRENT



REVERSE VOLTAGE (V)





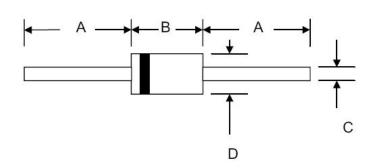


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Mechanical Dimensions R-1



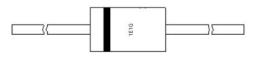
SYMBOL	Millin	neters	Inches			
	Min.	Max.	Min.	Max.		
A	25.4	-	1.000	-		
В	2.9	3.5	0.114	0.140		
С	0.55	0.65	0.021	0.025		
D	2.3	2.6	0.091	0.102		

Ordering Information

Device	Package	Shipping
1E1G-1E8G	R-1(Pb-Free)	5000pcs / tape
1E1GTA-1E8GTA	R-1(Pb-Free)	5000pcs / tape
1E1GTR-1E8GTR	R-1(Pb-Free)	5000pcs / reel

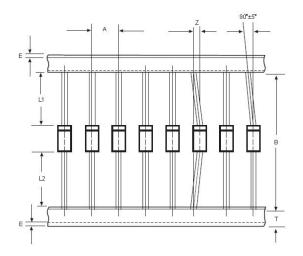
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



1E1G = Part Name

Carrier Tape Specification R-1



SYMBOL	Millimeters			
	Min.	Max.		
A	9.5	10.5		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
E	-	0.80		
IL1-L2I	_	1.0		



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